

Application Specific Discretes A.S.D.<sup>TM</sup>

#### FEATURES AND BENEFITS

- UNIDIRECTIONAL OVERVOLTAGE SUP-PRESSOR PROGRAMMABLE BY VOLTAGE AND CURRENT:
- PROGRAMMABLE BREAKDOWN VOLTAGE UP TO 100 V.
- PROGRAMMABLE CURRENT LIMITATION FROM 120 mA TO 600 mA.
- MULTI-LINE PROTECTION MODE : ONE DE-VICE CAN PROTECT SEVERALLINES.
- HIGH SURGE CURRENT CAPABILITY : IPP = 100A for 10/1000 μs.

#### DESCRIPTION

Dedicated to the protection of sensitive telecom equipment, the LCP3121 provides protection which can be programmed by both voltage and current.

The breakdown voltage can be easily programmed by using an external zener diode.

The protection function programmed by the current is achieved with the use of a resistor between the gate and the cathode. The value of the resistor will determine the level of the desired current before the triggering of the device.

A multiple protection mode is also performed when using several diodes providing each line interface with an optimized protection level.

If desired, a bidirectional protection function can be achieved by the use of two LCP3121.

### ${\small \mathsf{COMPLIESWITH}}\ {\small \mathsf{THE}}\ {\small \mathsf{FOLLOWING}}\ {\small \mathsf{STANDARDS}}\ :$

CCITT K20 :	10/700µs	1kV
VDE 0433 :	5/310μs 10/700μs 5/310μs	25A 2kV 50A
VDE 0878 :	1.2/50μs 1/20μs	1.5kV 40A
FCC part 68 :	2/10μs 2/10μs	2.5kV 200A (*)
BELLCORE	•	
TR-NWT-001089 :	2/10μs 2/10μs	2.5kV 200A (*)
BELLCORE		
TR-NWT-000974 :	10/1000μs 10/1000μs	1kV 100A
(*) with series resistors or PTC.		

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## OVERVOLTAGE AND OVERCURRENT PROTECTION FOR TELECOM LINE



#### **PIN-OUT CONFIGURATION**



#### **FUNCTIONAL DIAGRAM**



### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^{\circ}C$ )

Symbol	Parameter	Value	Unit	
Ipp	Peak pulse current (see note 1) 10/1000µs		100	А
Itsm	Non repetitive surge peak on-state current $t_p = 10ms$ (F = 50 Hz) $t = 1s$		16 8	A
Vac Vga	Maximum voltage between A and C Maximum voltage between G (Gn or Gp) and A	100 80	V	
T <sub>stg</sub> Tj	Storage temperature range Maximum junction temperature		- 40 to + 150 150	°C
TL	Maximum lead temperature for soldering during 10s		260	°C

#### Note 1 : Pulse waveform :

 $10/1000\mu s$   $t_r=10\mu s$   $t_p=1000\mu s$ 



#### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	170	°C/W

### **ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25 \degree C$ )

Symbol	Parameter	
V <sub>RM</sub>	Stand-off voltage	
V <sub>BR</sub>	Breakdown voltage	
VBO	Breakovervoltage	
lΗ	Holding current	
IBO	Breakover current	
I <sub>RM</sub>	Leakage current at V <sub>RM</sub>	
IR	Leakage current at VR	
I <sub>PP</sub>	Peak pulse current	
VR	Continuous reverse voltage	
Coff	Off-state capacitance	
VG	Gatevoltage	
Igp	Gp triggering current	
I <sub>GN</sub>	Gn triggering current	



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### 1 - OPERATION WITHOUT GATE (Tamb = 25 $^\circ C)$

Symbol	Test conditions	Min.	Max.	Unit
I <sub>RM</sub>	$V_{RM} = 60V$ $V_{RM} = 90V$		5 8	μA
I <sub>R</sub>	at VR = 180V		50	μA
V <sub>BR</sub>	at 1mA	100		V
IBO		80	500	mA
V <sub>BO</sub>	Measured at 50Hz		180	V
Iн	See the functional test circuit	100		mA
С	V <sub>R</sub> =-5V F=1MHz		100	pF

### 2 - OPERATION WITH GATE (Tamb = 25 °C)

Symbol	Test conditions	Min.	Max.	Unit
V <sub>G</sub> note1	IGATE = 200mA (for eigher Gn or Gp)	0.6	1.8	V
I <sub>GP</sub>	VAnode-cathode = 60V		180	mA
I <sub>GN</sub>	VAnode-cathode = 60V	80	200	mA

Note 1 : VG = VGN, measured between Gn and cathode VG = VGP, measured between Gp and anode

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### FUNCTIONAL HOLDING CURRENT (I<sub>H</sub>) TEST CIRCUIT : GO-NO GO TEST



Fig. 1 : Maximum non repetitive surge peak-onstate current versus overload duration.







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### **APPLICATION EXAMPLES**

Application 1 : Common protection for SLIC without integrated ring generator



Application 3 : Typical SLIC protection





Application 2 : Common protection for SLIC with integrated ring generator

Application 4 : Protection programmed by current



#### **ORDER CODE**



### PACKAGE MECHANICAL DATA

SO8 Plastic



	DIMENSIONS					
REF.	Millimetres		Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С		0.50			0.020	
c1	45° (typ)					
D	4.8		5.0	0.189		0.197
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max)					

#### MARKING

Package	Туре	Marking
SO8	LCP3121	CP3121

**Weight =** 0.08 g

**Packaging:** Products supplied in anti-static tubes or tape and reel.

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